

TOSHIBA**TC74VHC373F/FW/FT**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VHC373F, TC74VHC373FW, TC74VHC373FT**OCTAL D-TYPE LATCH WITH 3-STATE OUTPUT**

The TC74VHC373 is an advanced high speed CMOS OCTAL LATCH with 3 - STATE OUTPUT fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

This 8-bit D-type latch is controlled by a latch enable input (LE) and a output enable input (\overline{OE}).

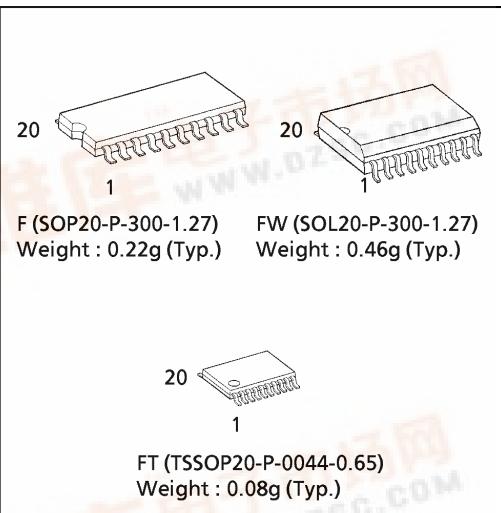
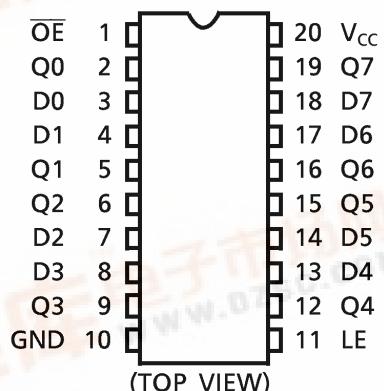
When the \overline{OE} input is high, the eight outputs are in a high impedance state.

An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

FEATURES :

- High Speed..... $t_{pd} = 5.0\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range..... $V_{CC} (\text{opr}) = 2\text{V} \sim 5.5\text{V}$
- Low Noise $V_{OLP} = 0.9\text{V}$ (Max.)
- Pin and Function Compatible with 74ALS373

(Note) The JEDEC SOP (FW) is not available in Japan.

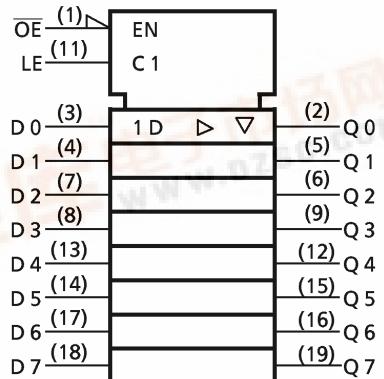
**PIN ASSIGNMENT****TRUTH TABLE**

INPUTS			OUTPUT
\overline{OE}	LE	D	
H	X	X	Z
L	L	X	Q_n
L	H	L	L
L	H	H	H

X : Don't Care

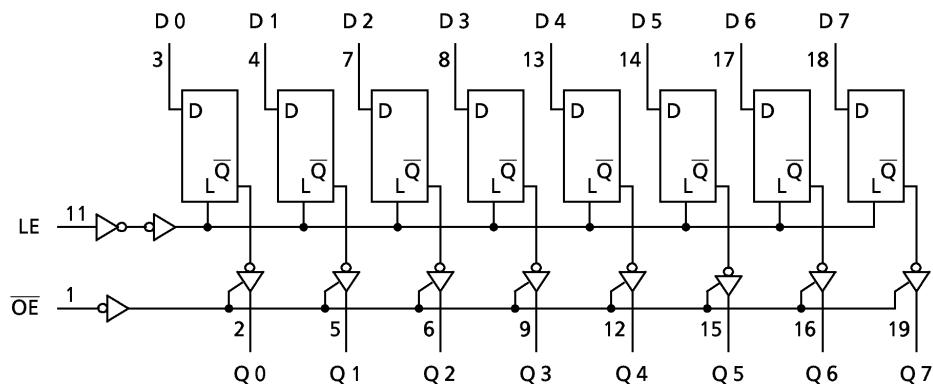
Z : High Impedance

Q_n : Q outputs are latched at the time when the LE input is taken to a low logic level.

IEC LOGIC SYMBOL

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SYSTEM DIAGRAM



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~7.0	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	-20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	180	mW
Storage Temperature	T_{STG}	-65~150	°C

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2.0~5.5	V
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{OPR}	-40~85	°C
Input Rise and Fall Time	dt/dv	0~100 ($V_{CC} = 3.3 \pm 0.3$ V) 0~20 ($V_{CC} = 5 \pm 0.5$ V)	ns/V

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 3.0~5.5 $V_{CC} \times 0.7$	1.50 — $V_{CC} \times 0.7$	— — —	— — —	1.50 $V_{CC} \times 0.7$ —	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 3.0~5.5 $V_{CC} \times 0.3$	— — $V_{CC} \times 0.3$	— — —	0.50 — —	0.50 $V_{CC} \times 0.3$ —	0.50 — —	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50\mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5	— — —	1.9 2.9 4.4	— — —
			$I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94	— —	— —	2.48 3.80	— —
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50\mu A$	2.0 3.0 4.5	— 0.0 0.0	0.0 0.1 0.1	0.1 — —	0.1 0.1 0.1	— — —
			$I_{OL} = 4mA$ $I_{OL} = 8mA$	3.0 4.5	— —	— —	0.36 0.36	— —	0.44 0.44
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5	—	—	± 0.25	—	± 2.50	μA
Input Leakage Current	I_{IN}	$V_{IN} = 5.5V$ or GND	0~5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	4.0	—	40.0	

TIMING REQUIREMENTS (Input $t_r = t_f = 3ns$)

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C		Ta = -40~85°C		UNIT
				TYP.	LIMIT	LIMIT	LIMIT	
Minimum Pulse Width (LE)	$t_W(H)$		3.3 ± 0.3 5.0 ± 0.5	— —	5.0 5.0	5.0 5.0	5.0 5.0	ns
Minimum Set - up Time	t_s		3.3 ± 0.3 5.0 ± 0.5	— —	4.0 4.0	4.0 4.0	4.0 4.0	
Minimum Hold Time	t_h		3.3 ± 0.3 5.0 ± 0.5	— —	1.0 1.0	1.0 1.0	1.0 1.0	

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -40~85°C		UNIT
		V _{CC} (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time (LE-Q)	t_{pLH} t_{pHL}	3.3 ± 0.3 5.0 ± 0.5	15	—	7.0	11.0	1.0	13.0	ns
			50	—	9.5	14.5	1.0	16.5	
			15	—	4.9	7.2	1.0	8.5	
			50	—	6.4	9.2	1.0	10.5	
Propagation Delay Time (D-Q)	t_{pLH} t_{pHL}	3.3 ± 0.3 5.0 ± 0.5	15	—	7.3	11.4	1.0	13.5	ns
			50	—	9.8	14.9	1.0	17.0	
			15	—	5.0	7.2	1.0	8.5	
			50	—	6.5	9.2	1.0	10.5	
3-State Output Enable Time	t_{pZL} t_{pZH}	3.3 ± 0.3 5.0 ± 0.5	15	—	7.3	11.4	1.0	13.5	ns
			50	—	9.8	14.9	1.0	17.0	
			15	—	5.5	8.1	1.0	9.5	
			50	—	7.0	10.1	1.0	11.5	
3-State Output Disable Time	t_{pLZ} t_{pHZ}	3.3 ± 0.3 5.0 ± 0.5	50	—	9.5	13.2	1.0	15.0	pF
			50	—	6.5	9.2	1.0	10.5	
Output to Output Skew	t_{osLH} t_{osHL}	3.3 ± 0.3 5.0 ± 0.5	50	—	—	1.5	—	1.5	pF
			50	—	—	1.0	—	1.0	
Input Capacitance	C_{IN}			—	4	10	—	10	pF
Output Capacitance	C_{OUT}			—	6	—	—	—	
Power Dissipation Capacitance	C_{PD}		(Note 2)	—	27	—	—	—	

Note (1) Parameter guaranteed by design. $t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLM} - t_{pHLn}|$

Note (2) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8 \text{ (per latch)}$$

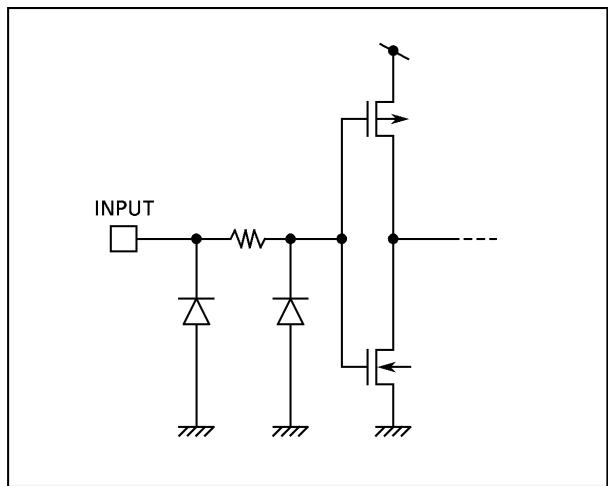
And the total C_{PD} when n pcs. of Latch operate can be gained by the following equation :

$$C_{PD} (\text{total}) = 14 + 13 \cdot n$$

NOISE CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

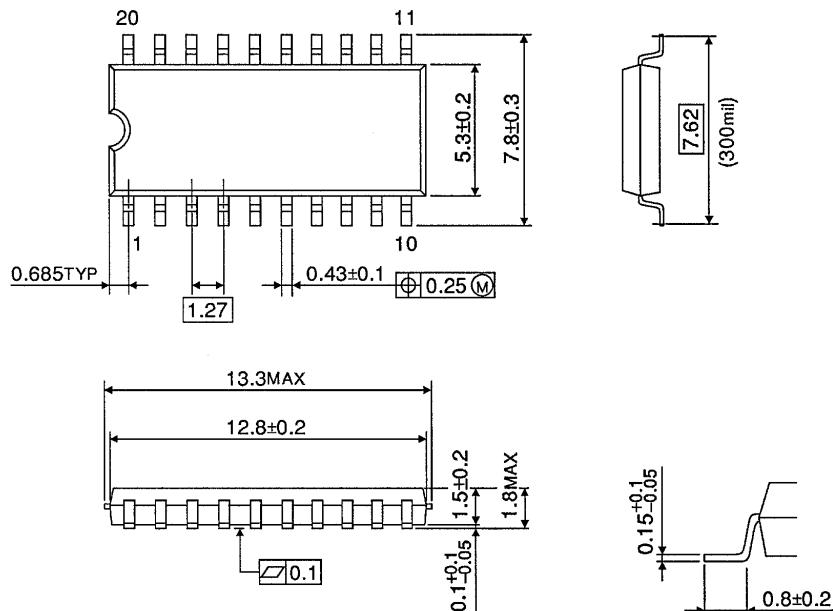
PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			UNIT
		V _{CC} (V)	TYP.	MAX.			
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$C_L = 50\text{pF}$	5.0	0.5 (0.6)	0.8 (0.9)	—	V
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	$C_L = 50\text{pF}$	5.0	-0.5 (-0.6)	-0.8 (-0.9)	—	V
Minimum High Level Dynamic Input Voltage	V_{IHD}	$C_L = 50\text{pF}$	5.0	—	3.5	—	V
Maximum Low Level Dynamic Input Voltage	V_{ILD}	$C_L = 50\text{pF}$	5.0	—	1.5	—	V

(Note) The value in () only applies to JEDEC SOP (FW) devices.

INPUT EQUIVALENT CIRCUIT

SOP 20PIN (200mil BODY) OUTLINE DRAWING (SOP20-P-300-1.27)

Unit in mm

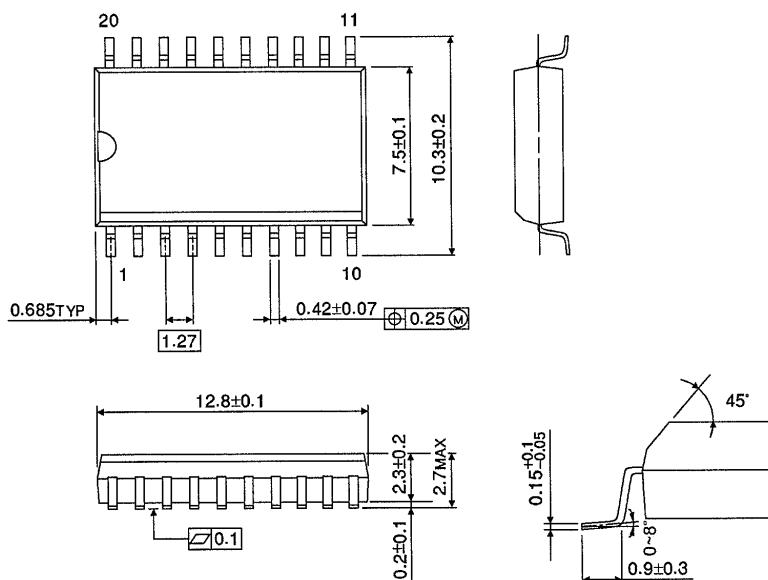


Weight : 0.22g (Typ.)

SOP 20PIN (300mil BODY) OUTLINE DRAWING (SOL20-P-300-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.46g (Typ.)

TSSOP 20PIN OUTLINE DRAWING (TSSOP20-P-0044-0.65)

Unit in mm

